

Product Summary (Typ @ $V_{GS} = -4.5V$, $T_A = +25^\circ C$)

BV_{DSS}	$R_{DS(ON)}$	I_D
-20V	37m Ω @ $V_{GS} = -4.5V$	-4.6A
	49m Ω @ $V_{GS} = -2.5V$	-3.7A

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Battery Management
- Load Switch
- Battery Protection

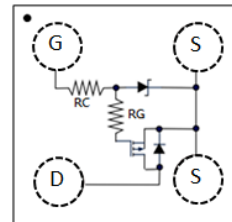
Features and Benefits

- Low Q_g & Q_{gd}
- Small Footprint
- Low Profile 0.62mm Height
- ESD Protected Up To 3kV
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)**
- Halogen and Antimony Free. "Green" Device (Note 3)**

Mechanical Data

- Case: U-WLB1010-4 (Type C)
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal: Finish - SnAgCu. Solderable per MIL-STD-202 Method 208 
- Terminal Connections: See Diagram Below

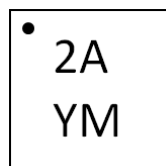
U-WLB1010-4 (Type C)


 Top View
 Equivalent Circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMP2042UCB4-7	U-WLB1010-4 (Type C)	3000/Tape & Reel

- Notes:
- No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
 - See <https://www.diodes.com/quality/lead-free/> for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 - Halogen and Antimony free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 - For packaging details, go to our website at <https://www.diodes.com/design/support/packaging/diodes-packaging/>.

Marking Information


2A = Product Type Marking Code
 YM = Date Code Marking
 Y or $\bar{Y}$ = Year (ex: F = 2018)
 M or $\bar{M}$ = Month (ex: 9 = September)

Date Code Key

Year	2016	2017	2018	2019	2020	2021	2022
Code	D	E	F	G	H	I	J

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Drain-Source Voltage	V _{DSS}	-20	V
Gate-Source Voltage	V _{GSS}	-6	V
Continuous Drain Current (Note 5) V _{GS} = -4.5V	I _D	-4.6	A
Continuous Drain Current (Note 5) V _{GS} = -2.5V	I _D	-3.7	A
Pulsed Drain Current (Note 6)	I _{DM}	-16	A

Thermal Characteristics

Characteristic	Symbol	Value	Unit
Power Dissipation (Note 7)	P _D	0.75	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 7)	R _{θJA}	165	°C/W
Power Dissipation (Note 5)	P _D	1.4	W
Thermal Resistance, Junction to Ambient @T _A = +25°C (Note 5)	R _{θJA}	87	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV _{DSS}	-20	—	—	V	V _{GS} = 0V, I _D = -250μA
Zero Gate Voltage Drain Current T _J = +25°C	I _{DSS}	—	—	-1	μA	V _{DS} = -16V, V _{GS} = 0V
Gate-Source Leakage	I _{GSS}	—	—	-100	nA	V _{GS} = -6V, V _{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	V _{GS(TH)}	-0.4	-0.8	-1.2	V	V _{DS} = V _{GS} , I _D = -250μA
Static Drain-Source On-Resistance	R _{DS(ON)}	—	37	45	mΩ	V _{GS} = -4.5V, I _D = -1A
		—	49	65		V _{GS} = -2.5V, I _D = -1A
Forward Transfer Admittance	Y _{FS}	—	6.6	-	S	V _{DS} = -10V, I _D = -1A
Diode Forward Voltage	V _{SD}	—	-0.7	-1.0	V	V _{GS} = 0V, I _S = -1A
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C _{iss}	—	218	—	pF	V _{DS} = -10V, V _{GS} = 0V, f = 1.0MHz
Output Capacitance	C _{oss}	—	148	—		
Reverse Transfer Capacitance	C _{rss}	—	11	—		
Series Gate Resistance	R _g	—	20	—	Ω	f = 1MHz, V _{GS} = 0V, V _{DS} = 0V
Series Clamp Resistance	R _C	—	5,000	—		
Total Gate Charge	Q _g	—	2.5	—	nC	V _{GS} = -4.5V, V _{DS} = -10V, I _D = -1A
Gate-Source Charge	Q _{gs}	—	0.4	—		
Gate-Drain Charge	Q _{gd}	—	0.4	—		
Gate Charge at V _{TH}	Q _{g(TH)}	—	0.2	—		
Turn-On Delay Time	t _{D(ON)}	—	0.6	—	μs	V _{DS} = -10V, V _{GS} = -2.5V, R _G = 10Ω, I _D = -1A
Turn-On Rise Time	t _r	—	0.8	—		
Turn-Off Delay Time	t _{D(OFF)}	—	1.4	—		
Turn-Off Fall Time	t _f	—	0.8	—		
Reverse Recovery Charge	Q _{RR}	—	2.2	—	nC	V _{DD} = -10V, I _F = -1.0A, di/dt = 100A/μs
Reverse Recovery Time	t _{RR}	—	10	—	ns	

- Notes:
- Device mounted on FR-4 material with 1-inch² (6.45-cm²), 2-oz. (0.071-mm thick) Cu.
 - Repetitive rating, pulse width limited by junction temperature.
 - Device mounted on FR-4 PCB with minimum recommended pad layout, single sided.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to production testing.

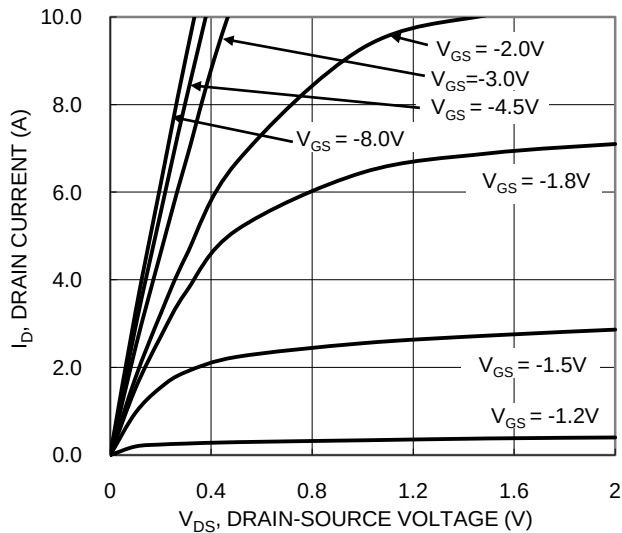


Figure 1. Typical Output Characteristic

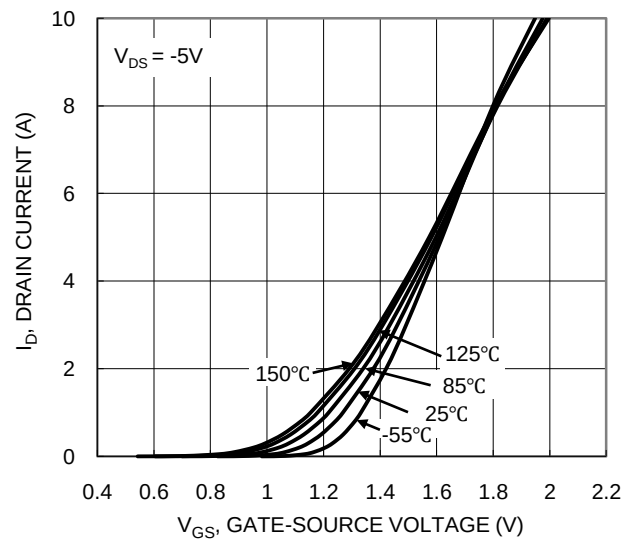


Figure 2. Typical Transfer Characteristic

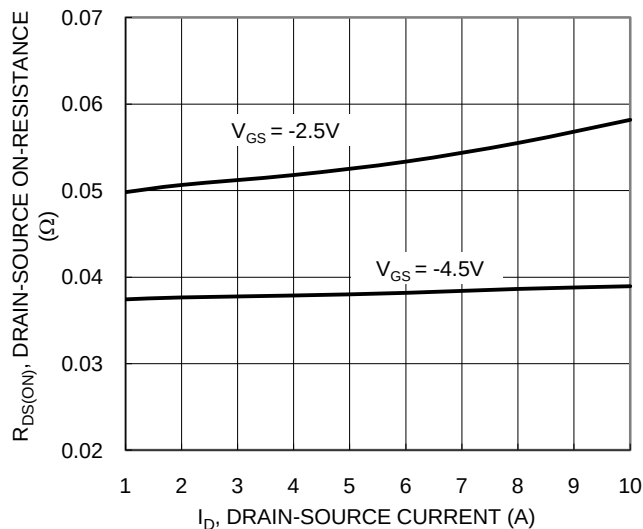


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

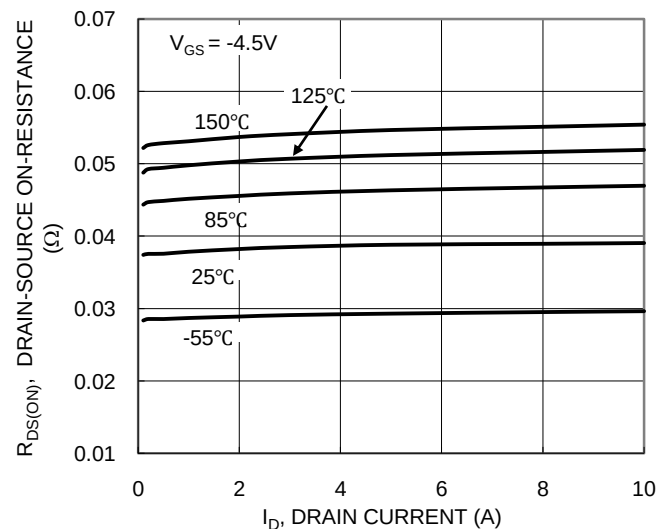


Figure 4. Typical On-Resistance vs. Drain Current and Junction Temperature

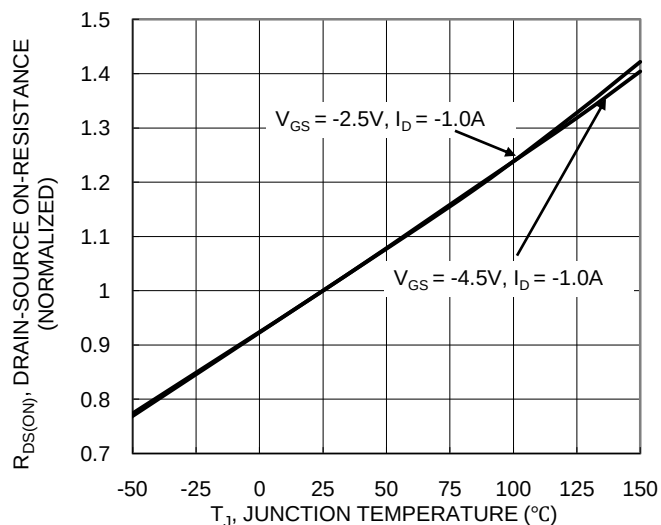


Figure 5. On-Resistance Variation with Junction Temperature

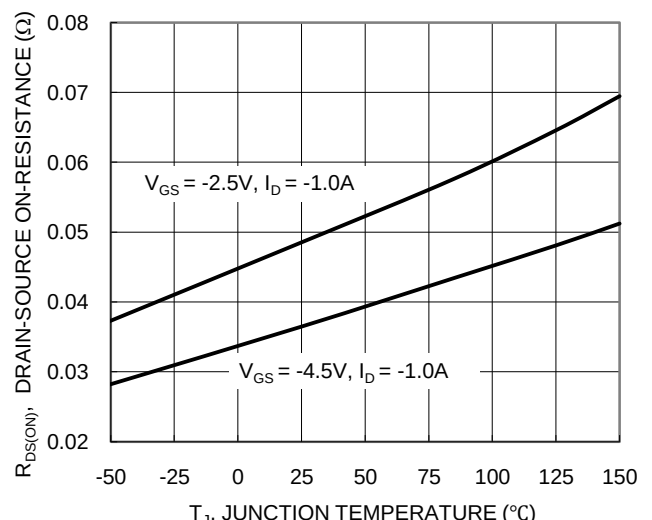


Figure 6. On-Resistance Variation with Junction Temperature

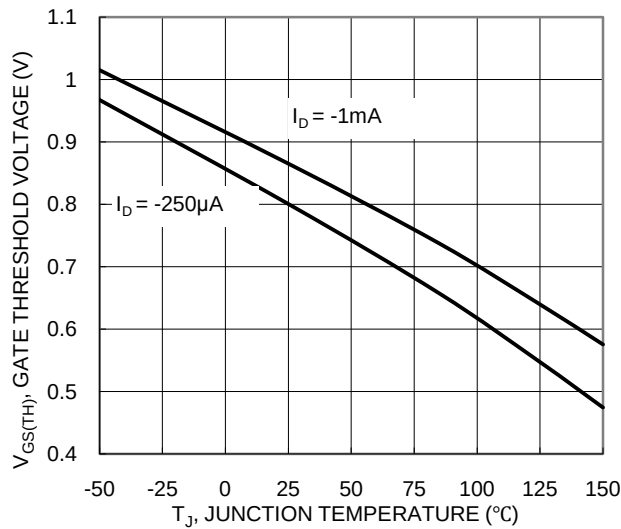


Figure 7. Gate Threshold Variation vs. Junction Temperature

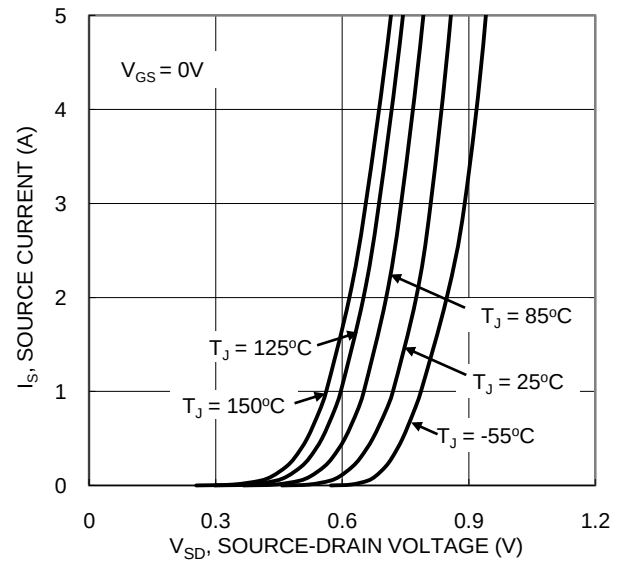


Figure 8. Diode Forward Voltage vs. Current

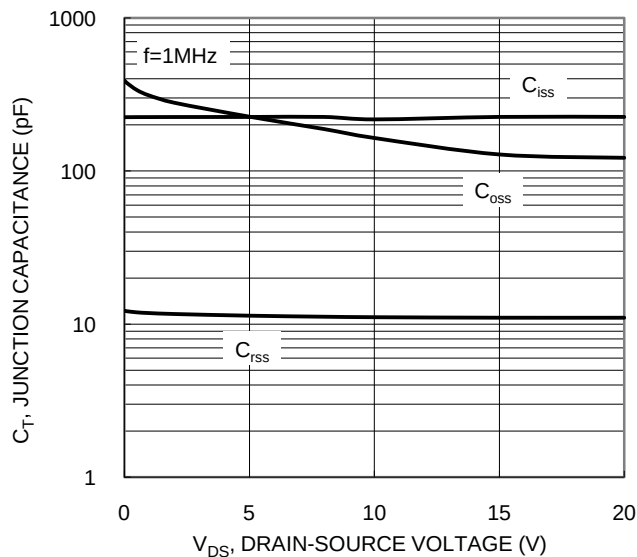


Figure 9. Typical Junction Capacitance

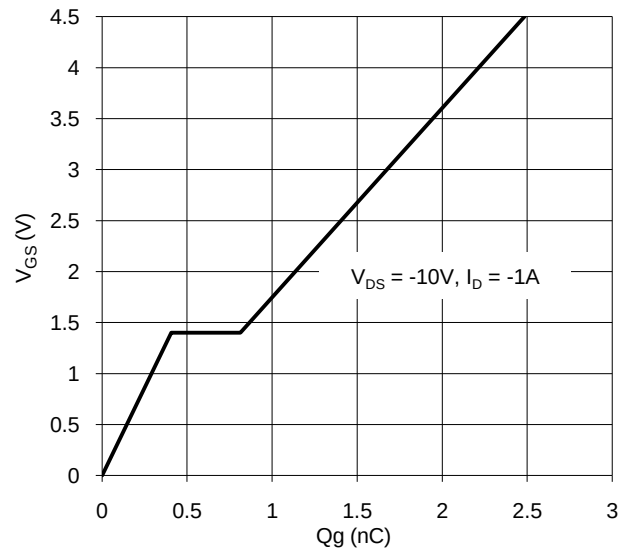


Figure 10. Gate Charge

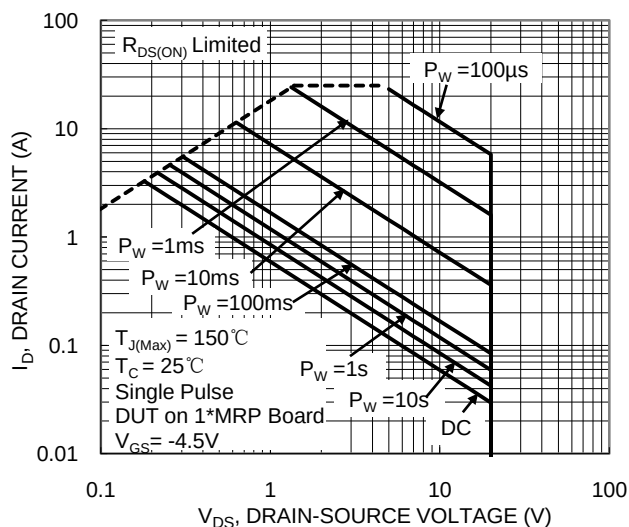


Figure 11. SOA, Safe Operation Area

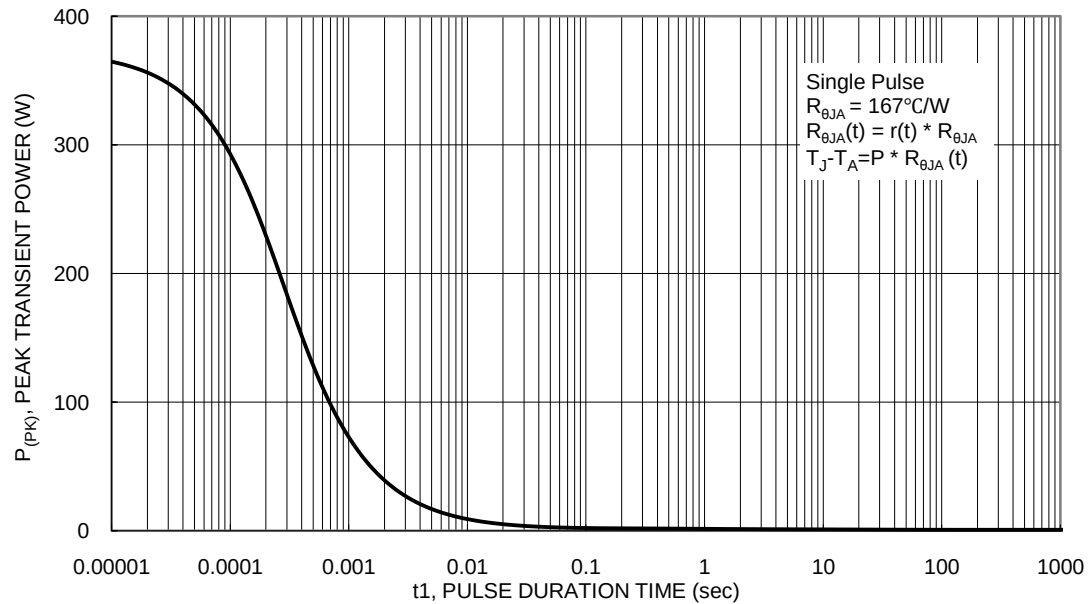


Figure 12. Single Pulse Maximum Power Dissipation

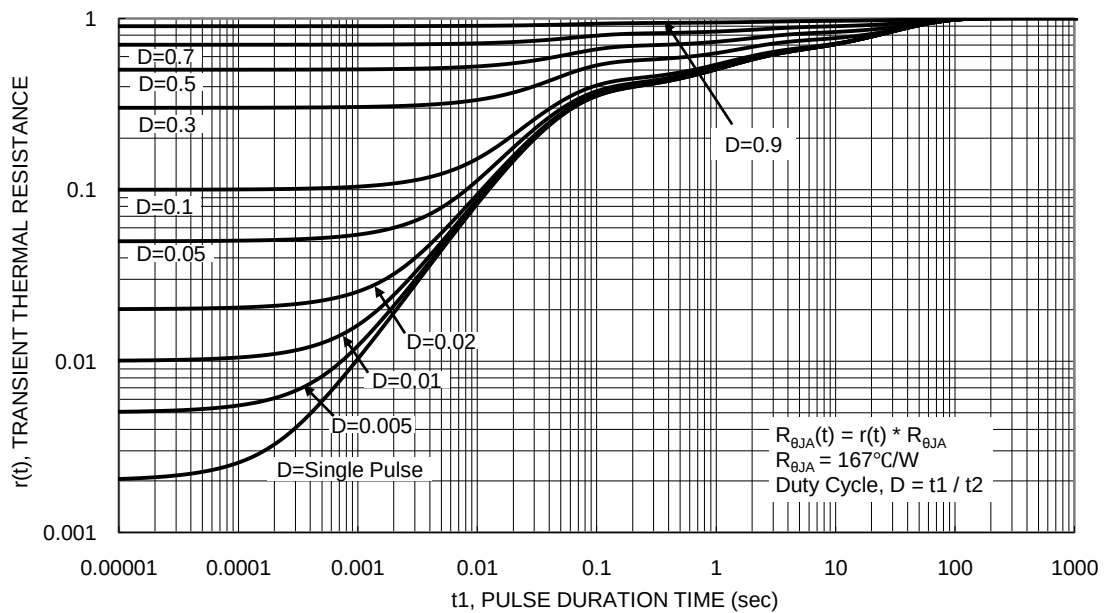
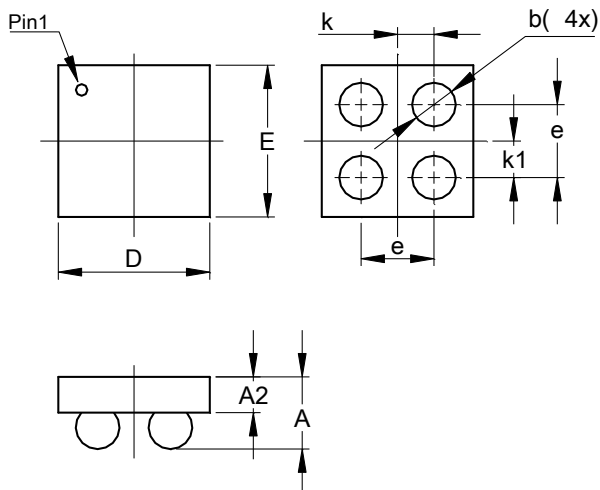


Figure 13. Transient Thermal Resistance

Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-WLB1010-4 (Type C)

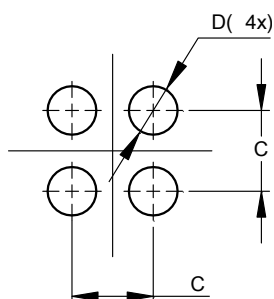


U-WLB1010-4 (Type C)			
Dim	Min	Max	Typ
A	--	0.62	--
A2	--	--	0.38
b	0.25	0.35	0.30
D	0.92	1.00	0.96
E	0.92	1.00	0.96
e	--	--	0.50
k	--	--	0.25
k1	--	--	0.25
All Dimensions in mm			

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

U-WLB1010-4 (Type C)



Dimensions	Value (in mm)
C	0.500
D	0.300

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